

# BAX12, BAX12A

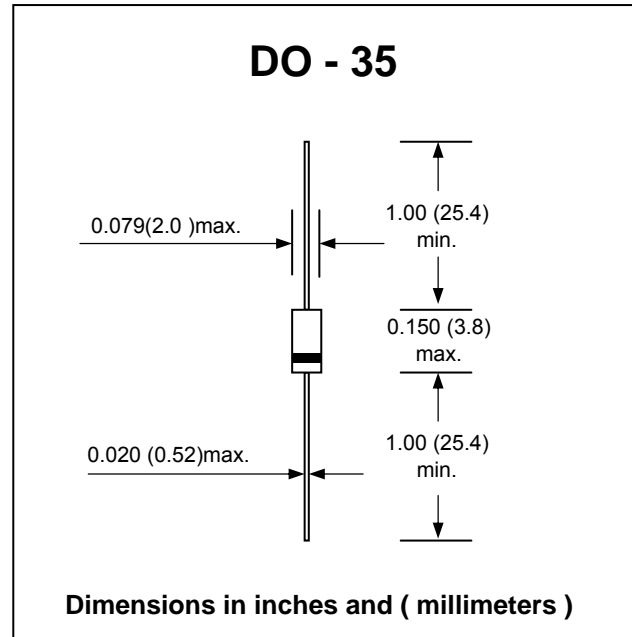
# CONTROLLED AVALANCHE DIODES

## FEATURES :

- \* Switching speed: max. 50 ns
- \* Continuous reverse voltage: max. 90V
- \* Repetitive peak reverse voltage: max. 90V
- \* Repetitive peak forward current: max.800 mA
- \* Repetitive peak reverse current: max.600mA
- \* Pb / RoHS Free

## MECHANICAL DATA :

- \* Case : DO-35 Glass Case
- \* Lead : Axial lead solderable per MIL-STD-202, Method 208 guaranteed
- \* Polarity : Color band denotes cathode end
- \* Mounting position : Any
- \* Weight : 0.13 gram (approximately)



## MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	90	V
Continuous Reverse Voltage	$V_R$	90	V
Continuous Forward Current	$I_F$	400	mA
Repetitive Peak Forward Current	$I_{FRM}$	800	A
Non-repetitive Peak Forward Current	$I_{FSM}$	55	A
Square wave: $T_j = 25\text{ }^\circ\text{C}$ prior to surge		$t = 1\text{ }\mu\text{s}$	
		$t = 100\text{ }\mu\text{s}$	
		9	
Total Power Dissipation , $T_a = 25\text{ }^\circ\text{C}$	$P_{tot}$	450	mW
Repetitive Peak Reverse Current	$I_{RRM}$	600	mA
Junction Temperature	$T_J$	200	$^\circ\text{C}$
Storage Temperature Range	$T_S$	-65 to + 200	$^\circ\text{C}$

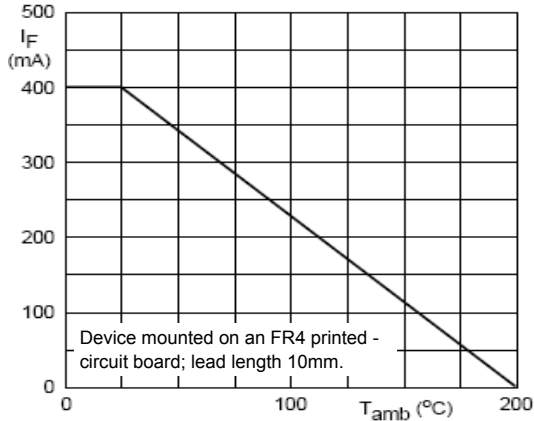
Note : (1) Device mounted on an FR4 printed circuit-board; lead length 10 mm.

## ELECTRICAL CHARACTERISTICS ( $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted)

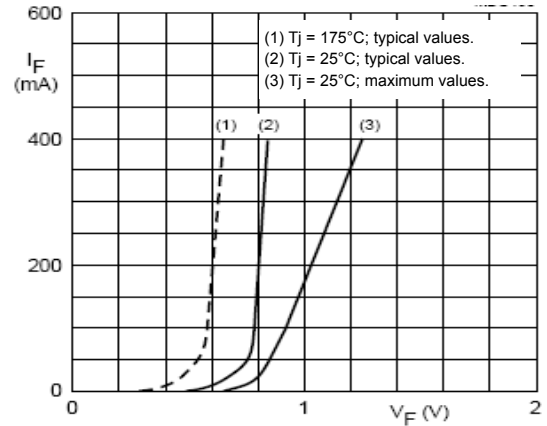
Parameter	Symbol	Test Condition	Min.	Max.	Unit
Reverse Avalanche Breakdown Voltage	$V_{(BR)R}$	$I_R = 1\text{ mA}$	120	170	V
		$I_R = 0.1\text{ mA}$	120	170	V
Reverse Current	$I_R$	$V_R = 90\text{ V}$	-	100	nA
		$V_R = 90\text{ V}, T_J = 150\text{ }^\circ\text{C}$	-	100	$\mu\text{A}$
Forward Voltage	$V_F$	$I_F = 400\text{ mA}$	-	1.25	V
Diode Capacitance	Cd	$f = 1\text{ MHz}; V_R = 0$	-	35	pF
Reverse Recovery Time	Trr	$I_F = 30\text{ mA}, I_R = 30\text{ mA}$ $R_L = 100\text{ }\Omega$ measured at $I_R = 3\text{ mA}$	-	50	ns

## RATING AND CHARACTERISTIC CURVES ( BAX12, BAX12A )

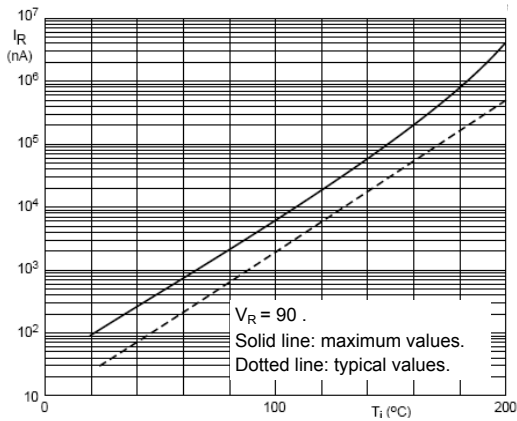
**Fig.1 - Maximum permissible continuous forward current as a function of ambient temperature.**



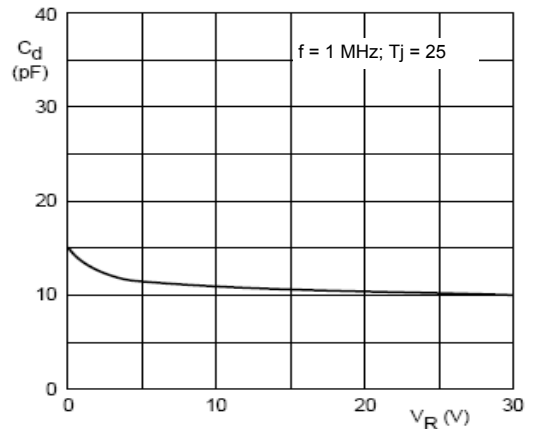
**Fig.2 - Forward current as a function of forward voltage.**



**Fig.3 - Reverse current as a function of junction temperature.**



**Fig.4 - Diode capacitance as a function of reverse voltage; typical values.**



**Fig.5 - Maximum permissible non-repetitive peak forward current as a function of pulse duration.**

